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#### Freescale Semiconductor

Data Sheet: Technical Data

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# **KL05 Sub-Family Data Sheet**

Supports: MKL05Z8VFK4, MKL05Z16VFK4, MKL05Z32VFK4, MKL05Z8VLC4, MKL05Z16VLC4, MKL05Z32VLC4, MKL05Z8VFM4, MKL05Z16VFM4, MKL05Z32VFM4, MKL05Z16VLF4, MKL05Z32VLF4

#### **Features**

- Operating Characteristics
  - Voltage range: 1.71 to 3.6 V
  - Flash write voltage range: 1.71 to 3.6 V
    Temperature range (ambient): -40 to 105°C
- Performance
  - Up to 48 MHz ARM® Cortex-M0+ core
- · Memories and memory interfaces
  - Up to 32 KB program flash memory
  - Up to 4 KB RAM
- Clocks
  - 32 kHz to 40 kHz or 3 MHz to 32 MHz crystal oscillator
  - Multi-purpose clock source
- System peripherals
  - Nine low-power modes to provide power optimization based on application requirements
  - 4-channel DMA controller, supporting up to 63 request sources
  - COP Software watchdog
  - Low-leakage wakeup unit
  - SWD interface and Micro Trace buffer
  - Bit Manipulation Engine (BME)

### KL05P48M48SF1



- Security and integrity modules
  - 80-bit unique identification (ID) number per chip
- Human-machine interface
  - Low-power hardware touch sensor interface (TSI)
  - General-purpose input/output
- · Analog modules
  - 12-bit SAR ADC
  - 12-bit DAC
  - Analog comparator (CMP) containing a 6-bit DAC and programmable reference input
- Timers
  - Two 2-channel Timer/PWM (TPM)
  - Periodic interrupt timers
  - 16-bit low-power timer (LPTMR)
  - Real-time clock
- Communication interfaces
  - One 8-bit SPI module
  - I2C module
  - One low power UART module



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## 1 Ordering parts

#### 1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: PKL05 and MKL05

#### 2 Part identification

### 2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

#### 2.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

#### 2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	<ul> <li>M = Fully qualified, general market flow</li> <li>P = Prequalification</li> </ul>
KL##	Kinetis family	• KL05
Α	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	<ul> <li>8 = 8 KB</li> <li>16 = 16 KB</li> <li>32 = 32 KB</li> </ul>
R	Silicon revision	<ul><li>(Blank) = Main</li><li>A = Revision after main</li></ul>

#### Terminology and guidelines

Field	Description	Values
Т	Temperature range (°C)	• V = -40 to 105
PP	Package identifier	<ul> <li>FK = 24 QFN (4 mm x 4 mm)</li> <li>LC = 32 LQFP (7 mm x 7 mm)</li> <li>FM = 32 QFN (5 mm x 5 mm)</li> <li>LF = 48 LQFP (7 mm x 7 mm)</li> </ul>
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz
N	Packaging type	<ul><li>R = Tape and reel</li><li>(Blank) = Trays</li></ul>

#### 2.4 Example

This is an example part number:

MKL05Z8VLC4

# 3 Terminology and guidelines

## 3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

## **3.1.1 Example**

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
$V_{DD}$	1.0 V core supply voltage	0.9	1.1	V

### 3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

#### 3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I <sub>WP</sub>	Digital I/O weak pullup/ pulldown current	10	130	μΑ

#### 3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

#### 3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	_	7	pF

# 3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

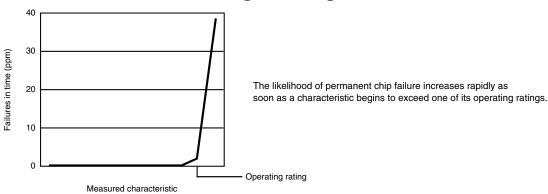
- Operating ratings apply during operation of the chip.
- Handling ratings apply when the chip is not powered.

#### **3.4.1 Example**

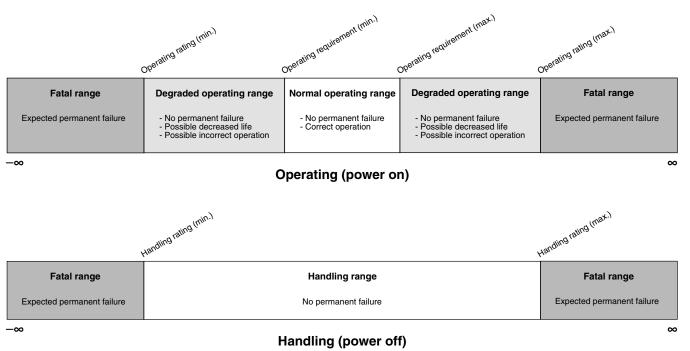
This is an example of an operating rating:

Symbol Description		Min.	Max.	Unit
$V_{DD}$	1.0 V core supply voltage	-0.3	1.2	V

# 3.5 Result of exceeding a rating



# 3.6 Relationship between ratings and operating requirements



### 3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

### 3.8 Definition: Typical value

A typical value is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

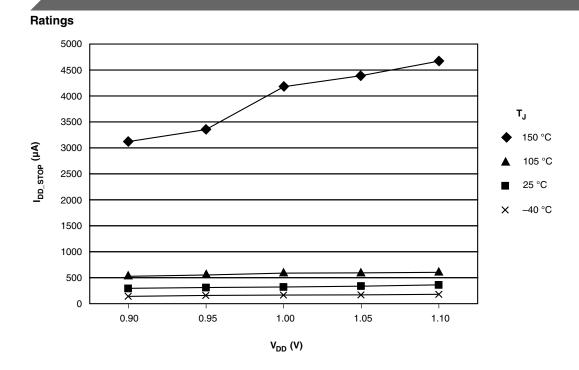
#### 3.8.1 **Example 1**

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Тур.	Max.	Unit
I <sub>WP</sub>	Digital I/O weak pullup/pulldown current	10	70	130	μΑ

### 3.8.2 **Example 2**

This is an example of a chart that shows typical values for various voltage and temperature conditions:



# 3.9 Typical Value Conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T <sub>A</sub>	Ambient temperature	25	°C
$V_{DD}$	3.3 V supply voltage	3.3	V

# 4 Ratings

# 4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T <sub>STG</sub>	Storage temperature	<b>-</b> 55	150	°C	1
T <sub>SDR</sub>	Solder temperature, lead-free	_	260	°C	2

<sup>1.</sup> Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.

<sup>2.</sup> Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

## 4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	_	3	_	1

Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

### 4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V <sub>HBM</sub>	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V <sub>CDM</sub>	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I <sub>LAT</sub>	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

- 1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
- 2. Determined according to JEDEC Standard JESD22-C101, Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.

#### 4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
$V_{DD}$	Digital supply voltage	-0.3	3.8	V
I <sub>DD</sub>	Digital supply current	_	120	mA
$V_{DIO}$	Digital pin input voltage (except RESET)	-0.3	V <sub>DD</sub> + 0.3	V
V <sub>AIO</sub>	Analog pins <sup>1</sup> and RESET pin input voltage	-0.3	V <sub>DD</sub> + 0.3	V
I <sub>D</sub>	Instantaneous maximum current single pin limit (applies to all port pins)	<del>-</del> 25	25	mA
$V_{DDA}$	Analog supply voltage	V <sub>DD</sub> – 0.3	V <sub>DD</sub> + 0.3	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

#### 5 General

#### 5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

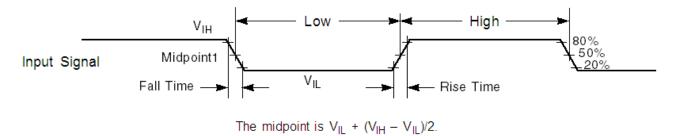


Figure 1. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume:

- 1. output pins
  - have  $C_L=30pF$  loads,
  - are slew rate disabled, and
  - are normal drive strength

# 5.2 Nonswitching electrical specifications

#### 5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
$V_{DD}$	Supply voltage	1.71	3.6	V	
$V_{DDA}$	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V <sub>DD</sub> -to-V <sub>DDA</sub> differential voltage	-0.1	0.1	V	
V <sub>SS</sub> – V <sub>SSA</sub>	V <sub>SS</sub> -to-V <sub>SSA</sub> differential voltage	-0.1	0.1	V	
$V_{IH}$	Input high voltage				
	• $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	$0.7 \times V_{DD}$	_	V	
	• 1.7 V ≤ V <sub>DD</sub> ≤ 2.7 V	$0.75 \times V_{DD}$	_	V	
V <sub>IL</sub>	Input low voltage				
	• 2.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	_	$0.35 \times V_{DD}$	V	
	• 1.7 V ≤ V <sub>DD</sub> ≤ 2.7 V	_	$0.3 \times V_{DD}$	V	
$V_{HYS}$	Input hysteresis	$0.06 \times V_{DD}$	_	V	

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I <sub>ICIO</sub>	I/O pin DC injection current — single pin				1
	<ul> <li>V<sub>IN</sub> &lt; V<sub>SS</sub>-0.3V (Negative current injection)</li> </ul>			mA	
	• V <sub>IN</sub> > V <sub>DD</sub> +0.3V (Positive current injection)	-3	_		
		_	+3		
I <sub>ICcont</sub>	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins				
	Negative current injection	-25	_	mA	
	Positive current injection	_	+25		
V <sub>RAM</sub>	V <sub>DD</sub> voltage required to retain RAM	1.2	_	V	

<sup>1.</sup> All analog pins are internally clamped to V<sub>SS</sub> and V<sub>DD</sub> through ESD protection diodes. If V<sub>IN</sub> is greater than V<sub>AIO\_MIN</sub> (=V<sub>SS</sub>-0.3V) and V<sub>IN</sub> is less than V<sub>AIO\_MAX</sub>(=V<sub>DD</sub>+0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R=(V<sub>AIO\_MIN</sub>-V<sub>IN</sub>)/II<sub>IC</sub>I. The positive injection current limiting resistor is calculated as R=(V<sub>IN</sub>-V<sub>AIO\_MAX</sub>)/II<sub>IC</sub>I. Select the larger of these two calculated resistances.

#### 5.2.2 LVD and POR operating requirements

Table 2. V<sub>DD</sub> supply LVD and POR operating requirements

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V <sub>POR</sub>	Falling V <sub>DD</sub> POR detect voltage	0.8	1.1	1.5	V	
$V_{LVDH}$	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
$V_{LVW1H}$	Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
$V_{LVW2H}$	Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
$V_{LVW3H}$	Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
$V_{LVW4H}$	Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V <sub>HYSH</sub>	Low-voltage inhibit reset/recover hysteresis — high range	_	±60	_	mV	
$V_{LVDL}$	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
$V_{LVW1L}$	Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
$V_{LVW2L}$	Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
$V_{LVW3L}$	Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
$V_{LVW4L}$	Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V <sub>HYSL</sub>	Low-voltage inhibit reset/recover hysteresis — low range	_	±40	_	mV	

Table 2. V<sub>DD</sub> supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V <sub>BG</sub>	Bandgap voltage reference	0.97	1.00	1.03	V	
t <sub>LPO</sub>	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

#### 5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V <sub>OH</sub>	Output high voltage — Normal drive pad				1
	• $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OH} = -5 \text{ mA}$	V <sub>DD</sub> – 0.5	_	V	
	• 1.71 V $\leq$ V <sub>DD</sub> $\leq$ 2.7 V, I <sub>OH</sub> = -1.5 mA	V <sub>DD</sub> – 0.5	_	V	
V <sub>OH</sub>	Output high voltage — High drive pad				1
	• $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OH} = -18 \text{ mA}$	V <sub>DD</sub> – 0.5	_	V	
	• 1.71 V $\leq$ V <sub>DD</sub> $\leq$ 2.7 V, I <sub>OH</sub> = -6 mA	$V_{DD} - 0.5$	_	V	
I <sub>OHT</sub>	Output high current total for all ports	_	100	mA	
V <sub>OL</sub>	Output low voltage — Normal drive pad				1
	• $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OL} = 5 \text{ mA}$	_	0.5	V	
	• 1.71 V $\leq$ V <sub>DD</sub> $\leq$ 2.7 V, I <sub>OL</sub> = 1.5 mA	_	0.5	V	
V <sub>OL</sub>	Output low voltage — High drive pad				1
	• $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OL} = 18 \text{ mA}$	_	0.5	V	
	• 1.71 V ≤ V <sub>DD</sub> ≤ 2.7 V, I <sub>OL</sub> = 6 mA	_	0.5	V	
I <sub>OLT</sub>	Output low current total for all ports	_	100	mA	
I <sub>IN</sub>	Input leakage current (per pin) for full temperature range	_	1	μA	2
I <sub>IN</sub>	Input leakage current (per pin) at 25 °C	_	0.025	μΑ	2
I <sub>IN</sub>	Input leakage current (total all pins) for full temperature range	_	41	μA	2
l <sub>OZ</sub>	Hi-Z (off-state) leakage current (per pin)	_	1	μA	
R <sub>PU</sub>	Internal pullup resistors	20	50	kΩ	3

<sup>1.</sup> PTA12, PTA13, PTB0 and PTB1 I/O have both high drive and normal drive capability selected by the associated PTx\_PCRn[DSE] control bit. All other GPIOs are normal drive only.

<sup>2.</sup> Measured at  $V_{DD} = 3.6 \text{ V}$ 

<sup>3.</sup> Measured at  $V_{DD}$  supply voltage =  $V_{DD}$  min and Vinput =  $V_{SS}$ 

## 5.2.4 Power mode transition operating behaviors

All specifications except  $t_{POR}$  and VLLSx $\rightarrow$ RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- FEI clock mode

Table 4. Power mode transition operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t <sub>POR</sub>	After a POR event, amount of time from the point $V_{DD}$ reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	_	_	300	μs	
	• VLLS0 → RUN	_	95	115	μs	
	• VLLS1 → RUN	_	93	115	μs	
	• VLLS3 → RUN	_	42	53	μs	
	• LLS → RUN	_	4	4.6	μs	
	VLPS → RUN	_	4	4.4	μs	
	• STOP → RUN	_	4	4.4	μs	

## 5.2.5 Power consumption operating behaviors

Table 5. Power consumption operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I <sub>DDA</sub>	Analog supply current	_	_	See note	mA	1
I <sub>DD_RUNCO</sub>	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash • at 3.0 V	_	4.1	5.2	mA	2
I <sub>DD_RUN</sub>	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash  • at 3.0 V	_	4.9	5.6	mA	2

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I <sub>DD_RUN</sub>	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash					2, 3
	• at 3.0 V		5.0	0.0	A	
	• at 25 °C	_	5.6	6.8	mA	
	• at 125 °C	_	6	7.2	mA	
I <sub>DD_WAIT</sub>	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	_	3.0	4.2	mA	2
I <sub>DD_WAIT</sub>	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	_	2.4	3.36	mA	2
I <sub>DD_PSTOP2</sub>	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus  • at 3.0 V	_	2.25	3.38	mA	2
I <sub>DD_VLPRCO</sub>	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash  • at 3.0 V	_	182	522	μА	4
I <sub>DD_VLPR</sub>	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash • at 3.0 V	_	213.33	577.8	μА	4
I <sub>DD_VLPR</sub>	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash  • at 3.0 V	_	242.8	631.8	μА	3, 4
I <sub>DD_VLPW</sub>	Very-low-power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	_	106.1	399.42	μА	4

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I <sub>DD_STOP</sub>	Stop mode current					
	• at 3.0 V					
	• at 25 °C	-	273	441		
	• at 50 °C	_	281.2	620	μΑ	
	• at 70 °C	_	301.6	647.64		
	• at 85 °C	_	331	710.64		
	• at 105 °C	_	406.6	1001.84		
I <sub>DD_VLPS</sub>	Very-low-power stop mode current • at 3.0 V					
	• at 25 °C	_	3.08	16.01		
	• at 50 °C	_	5.46	34.73	μA	
	• at 70 °C		12.08	46.73	m''	
	• at 85 °C		22.89	77.37		
	• at 105 °C	_	53.24	190.28		
I <sub>DD_LLS</sub>	Low-leakage stop mode current  • at 3.0 V		00.21	100.20		
	• at 25 °C		4 -	0.00		
	• at 50 °C	-	1.7	3.69		
	• at 70 °C	_	3	22	μΑ	
	• at 85 °C	_	5.8	28.19		
	• at 105 °C		10.4	40.29		
		_	24	65.5		
I <sub>DD_VLLS3</sub>	Very-low-leakage stop mode 3 current  • at 3.0 V				μΑ	
	• at 25 °C		1.3	3		
	• at 50 °C		2.3	11.04		
	• at 70 °C		4.4	13.68		
	• at 85 °C		8	20.14		
	• at 105 °C		18.6	37.82		
I <sub>DD_VLLS1</sub>	Very-low-leakage stop mode 1 current  • at 3.0 V		10.0	37.02		
	• at 25°C		0.70			
	• at 50°C		0.78	1.6		
	• at 70°C		1.5	13.61	μΑ	
	• at 85°C		3.3	15.59		
	• at 105°C		6.3	16.68		
	4.100 0		15.2	26.40		

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I <sub>DD_VLLS0</sub>	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 0) • at 3.0 V					
	• at 25 °C					
	• at 50 °C	_	449.6	959.2	nA	
	• at 70 °C	_	1200	12155.08		
	• at 85 °C	_	2900	15323.29		
	• at 105 °C	_	5900	16384.55		
	2	_	14800	26773.45		
I <sub>DD_VLLS0</sub>	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 1) • at 3.0 V					5
	• at 25 °C					
	• at 50 °C	_	221.7	894.24	nA	
	• at 70 °C	_	1000	3784.55		
	• at 85 °C	_	2600	12018.39		
	• at 105 °C	_	5600	18722.23		
		_	14400	24665.06		

<sup>1.</sup> The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.

Table 6. Low power mode peripheral adders — typical value

Symbol	Description		Temperature (°C)					Unit
		-40	25	50	70	85	105	
I <sub>IREFSTEN4MHz</sub>	4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.	56	56	56	56	56	56	μА
I <sub>IREFSTEN32KHz</sub>	32 kHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 32 kHz IRC enabled.	52	52	52	52	52	52	μА
I <sub>EREFSTEN4MHz</sub>	External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.	206	228	237	245	251	258	uA

<sup>2.</sup> MCG configured for FEI mode.

<sup>3.</sup> Incremental current consumption from peripheral activity is not included.

<sup>4.</sup> MCG configured for BLPI mode.

<sup>5.</sup> No brownout

Table 6. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	1
IEREFSTEN32KHZ	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled.							
	VLLS1	440	490	540	560	570	580	
	VLLS3	440	490	540	560	570	580	
	LLS	490	490	540	560	570	680	n
	VLPS							"
	STOP	510	560	560	560	610	680	
I <sub>CMP</sub>	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	510 22	560 22	22	22	22	22	μ
I <sub>RTC</sub>	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	432	357	388	475	532	810	n
I <sub>UART</sub>	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.  MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μ
	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I <sub>TPM</sub>	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.							μ
	MCGIRCLK (4 MHz internal reference clock)	86	86	86	86	86	86	
	OSCERCLK (4 MHz external crystal)	235	256	265	274	280	287	
I <sub>BG</sub>	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μ

#### General

Table 6. Low power mode peripheral adders — typical value (continued)

Symbol	Description		Temperature (°C)					Unit
		-40	25	50	70	85	105	
l <sub>ADC</sub>	ADC peripheral adder combining the measured values at V <sub>DD</sub> and V <sub>DDA</sub> by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μА

### 5.2.5.1 Diagram: Typical IDD\_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

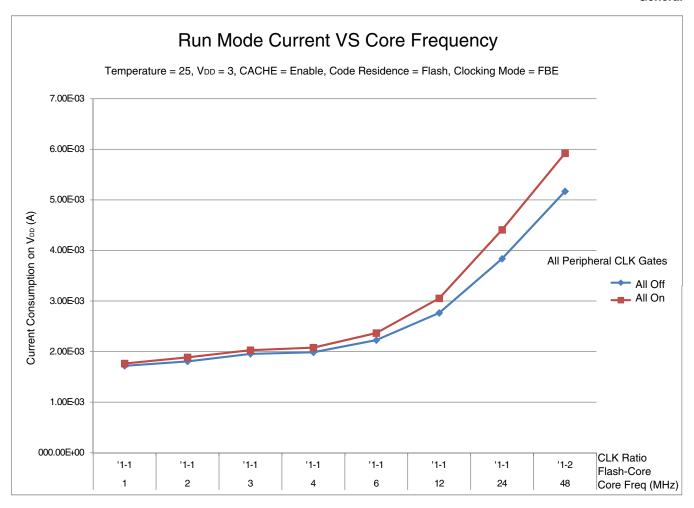


Figure 2. Run mode supply current vs. core frequency

#### General

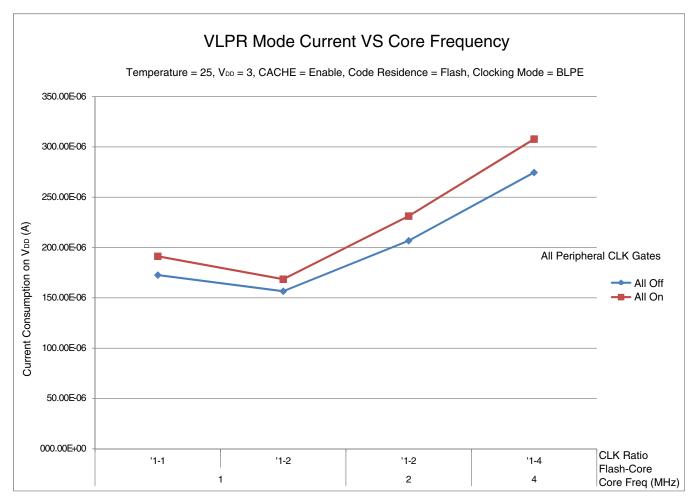


Figure 3. VLPR mode current vs. core frequency

## 5.2.6 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- 1. Go to www.freescale.com.
- 2. Perform a keyword search for "EMC design."

#### 5.2.7 Capacitance attributes

Table 7. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C <sub>IN_A</sub>	Input capacitance: analog pins	_	7	pF
C <sub>IN_D</sub>	Input capacitance: digital pins	_	7	pF

# 5.3 Switching specifications

## 5.3.1 Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
	Normal run mod	е	•		•
f <sub>SYS</sub>	System and core clock	_	48	MHz	
f <sub>BUS</sub>	Bus clock	_	24	MHz	
f <sub>FLASH</sub>	Flash clock	_	24	MHz	
f <sub>LPTMR</sub>	LPTMR clock	_	24	MHz	
	VLPR mode <sup>1</sup>				
f <sub>SYS</sub>	System and core clock	_	4	MHz	
f <sub>BUS</sub>	Bus clock	_	1	MHz	
f <sub>FLASH</sub>	Flash clock	_	1	MHz	
f <sub>LPTMR</sub>	LPTMR clock	_	24	MHz	
f <sub>ERCLK</sub>	External reference clock	_	16	MHz	
f <sub>LPTMR_pin</sub>	LPTMR clock	_	24	MHz	
f <sub>LPTMR_ERCL</sub> K	LPTMR external reference clock	_	16	MHz	
f <sub>osc_hi_2</sub>	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	_	16	MHz	
f <sub>TPM</sub>	TPM asynchronous clock	_	8	MHz	
f <sub>UART0</sub>	UART0 asynchronous clock	_	8	MHz	

<sup>1.</sup> The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

#### 5.3.2 General Switching Specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and I<sup>2</sup>C signals.

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	_	Bus clock cycles	1
	External RESET and NMI pin interrupt pulse width — Asynchronous path	100	_	ns	2
	GPIO pin interrupt pulse width — Asynchronous path	16	_	ns	2
	Port rise and fall time				3
		_	36	ns	

#### General

- 1. The greater synchronous and asynchronous timing must be met.
- 2. This is the shrtest pulse that is guaranteed to be recognized.
- 3. 75 pF load

### 5.4 Thermal specifications

### 5.4.1 Thermal operating requirements

Table 8. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
TJ	Die junction temperature	-40	125	°C
T <sub>A</sub>	Ambient temperature	-40	105	°C

#### 5.4.2 Thermal attributes

Table 9. Thermal attributes

Board type	Symbol	Description	48 LQFP	32 LQFP	32 QFN	24 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	82	88	97	110	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	58	59	34	42	°C/W	
Single-layer (1S)	R <sub>θJMA</sub>	Thermal resistance, junction to ambient (200 ft./min. air speed)	70	74	81	92	°C/W	
Four-layer (2s2p)	R <sub>θJMA</sub>	Thermal resistance, junction to ambient (200 ft./min. air speed)	52	52	28	36	°C/W	
_	R <sub>θJB</sub>	Thermal resistance, junction to board	36	35	13	18	°C/W	2
_	R <sub>0JC</sub>	Thermal resistance, junction to case	27	26	2.3	3.7	°C/W	3
_	$\Psi_{ m JT}$	Thermal characterization parameter, junction to package top outside center (natural convection)	8	8	8	10	°C/W	4

<sup>1.</sup> Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air), or EIA/JEDEC Standard JESD51-6, Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air).

<sup>2.</sup> Determined according to JEDEC Standard JESD51-8, Integrated Circuit Thermal Test Method Environmental Conditions —Junction-to-Board.

- 3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
- 4. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air).

# 6 Peripheral operating requirements and behaviors

#### 6.1 Core modules

#### 6.1.1 SWD Electricals

Table 10. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	_	ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	_	ns
J4	SWD_CLK rise and fall times	_	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	_	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	_	ns
J11	SWD_CLK high to SWD_DIO data valid	_	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	_	ns

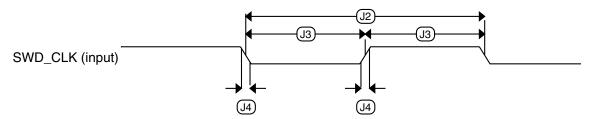


Figure 4. Serial wire clock input timing

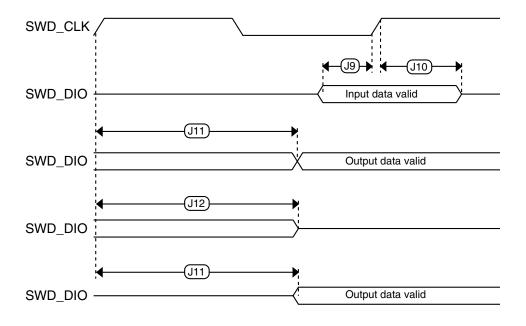


Figure 5. Serial wire data timing

# 6.2 System modules

There are no specifications necessary for the device's system modules.

#### 6.3 Clock modules

# 6.3.1 MCG specifications

Table 11. MCG specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f <sub>ints_ft</sub>	Internal reference frequency (slow clock) — factory trimmed at nominal V <sub>DD</sub> and 25 °C	_	32.768	_	kHz	
f <sub>ints_t</sub>	Internal reference frequency (slow clock) — user trimmed	31.25	_	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	_	± 0.3	± 0.6	%f <sub>dco</sub>	1
$\Delta f_{dco\_t}$	Total deviation of trimmed average DCO output frequency over voltage and temperature	_	+0.5/-0.7	± 3	%f <sub>dco</sub>	1, 2

Table 11. MCG specifications (continued)

Symbol	Description		Min.	Тур.	Max.	Unit	Notes
$\Delta f_{dco\_t}$	Total deviation of t frequency over fixe range of 0 - 70 °C	_	± 0.4	± 1.5	%f <sub>dco</sub>	1, 2	
f <sub>intf_ft</sub>		frequency (fast clock) — nominal V <sub>DD</sub> and 25 °C	_	4	_	MHz	
$\Delta f_{intf\_ft}$	(fast clock) over te	on of internal reference clock mperature and voltage — nominal V <sub>DD</sub> and 25 °C	_	+1/-2	± 3	%f <sub>intf_ft</sub>	2
f <sub>intf_t</sub>	Internal reference frequency (fast clock) — user trimmed at nominal V <sub>DD</sub> and 25 °C		3	_	5	MHz	
f <sub>loc_low</sub>	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f <sub>ints_t</sub>	_	_	kHz	
f <sub>loc_high</sub>	Loss of external cle RANGE = 01, 10, o	(16/5) x f <sub>ints_t</sub>	_	_	kHz		
		F	LL				
$f_{fII\_ref}$	FLL reference freq	uency range	31.25	_	39.0625	kHz	
$f_{dco}$	DCO output frequency range	Low range (DRS = 00) $640 \times f_{fil\_ref}$	20	20.97	25	MHz	3, 4
		Mid range (DRS = 01) $1280 \times f_{fll\_ref}$	40	41.94	48	MHz	
dco_t_DMX32	DCO output frequency	Low range (DRS = 00) $732 \times f_{fil\_ref}$	_	23.99	_	MHz	5, 6
		Mid range (DRS = 01) $1464 \times f_{fll\_ref}$	_	47.97	_	MHz	
J <sub>cyc_fll</sub>	FLL period jitter  • f <sub>VCO</sub> = 48 MHz		_	180	_	ps	7
t <sub>fll_acquire</sub>			_	_	1	ms	8
-iii_acquire	FLL target frequency acquisition time				1 '	0	

- This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
- 2. The deviation is relative to the factory trimmed frequency at nominal  $V_{DD}$  and 25 °C,  $f_{ints\_ft}$ .
- 3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
- The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation
   (Δf<sub>dco\_t</sub>) over voltage and temperature must be considered.
- 5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
- 6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- 7. This specification is based on standard deviation (RMS) of period or frequency.
- 8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

#### 6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.